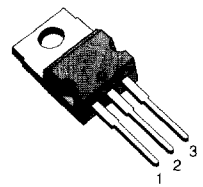
SGS-THOMSON MICROELECTRONICS

STP55N06
STP55N06FI

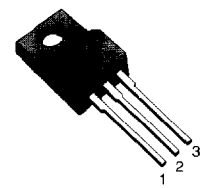
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STP55N06	60 V	0.023 Ω	55 A
STP55N06FI	60 V	0.023 Ω	30 A

- AVALANCHE RUGGEDNESS TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE FOR STANDARD PACKAGE
- VERY LOW $R_{DS(on)}$
- APPLICATION ORIENTED CHARACTERIZATION
- ISOLATED PACKAGE UL RECOGNIZED, ISOLATION TO 2000V DC



TO-220

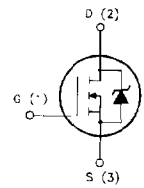


ISOWATT220

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP55N06	STP55N06FI	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	60		V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	60		V
V_{GS}	Gate-source Voltage	± 20		V
I_D	Drain Current (continuous) at T_c = 25 °C(#)	55	30	A
I_D	Drain Current (continuous) at T_c = 100 °C	41	19	A
I_{DM}(•)	Drain Current (pulsed)	220	220	A
P_{tot}	Total Dissipation at T_c = 25 °C	150	40	W
	Derating Factor	1	0.32	W/°C
T_{stg}	Storage Temperature	-65 to 175	-65 to 150	°C
T_j	Max. Operating Junction Temperature	175	150	°C

(•) Pulse width limited by safe operating area
(#) T_c = 50 °C for TO-220

THERMAL DATA

			TO-220	ISOWATT220	
$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	1	3.12	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	62.5		°C/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	0.5		°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	55	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 25 V)	520	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	130	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (T_c = 100 °C, pulse width limited by T_j max, $\delta < 1\%$)	34	A

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	60			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating x 0.8 T_c = 125 °C			250 1000	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ I_D = 250 µA	2		4	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 30 A V_{GS} = 10 V I_D = 30 A T_c = 100°C			0.023 0.046	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ V_{GS} = 10 V	55			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ I_D = 30 A	16			S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0		2500 950 250	3000 1200 350	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	V_{DD} = 40 V I_D = 55 A		110	150	ns
t_r	Rise Time	R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 3)		300	400	ns
$(di/dt)_{on}$	Turn-on Current Slope	V_{DD} = 40 V I_D = 55 A R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 5)		160		A/µs
Q_g	Total Gate Charge	V_{DD} = 25 V I_D = 30 A V_{GS} = 10 V		65	90	nC

SWITCHING OFF

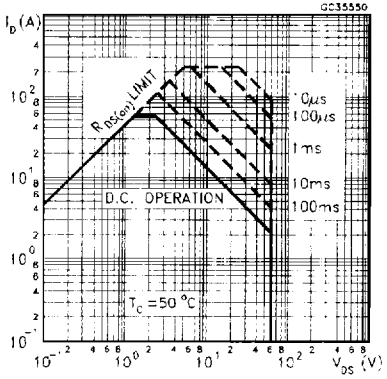
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	V_{DD} = 40 V I_D = 55 A		160	220	ns
t_f	Fall Time	R_G = 50 Ω V_{GS} = 10 V		160	220	ns
t_c	Cross-over Time	(see test circuit, figure 5)		320	440	ns

SOURCE DRAIN DIODE

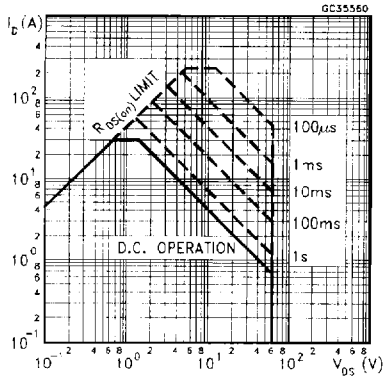
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				55	A
I_{SDM}(•)	Source-drain Current (pulsed)				220	A
V_{SD} (*)	Forward On Voltage	I_{SD} = 55 A V_{GS} = 0			1.6	V
t_{rr}	Reverse Recovery Time	I_{SD} = 55 A di/dt = 100 A/µs V_{DD} = 25 V T_j = 150 °C		100		ns
Q_{rr}	Reverse Recovery Charge	(see test circuit, figure 5)		0.25		µC
I_{RRM}	Reverse Recovery Current			5		A

(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %
(•) Pulse width limited by safe operating area

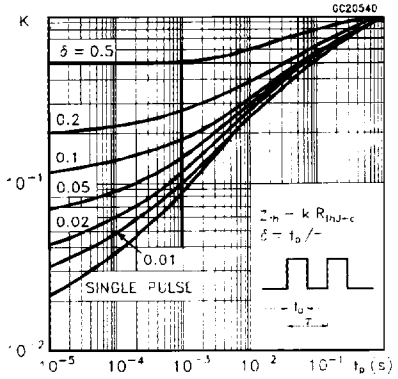
Safe Operating Areas For TO-220



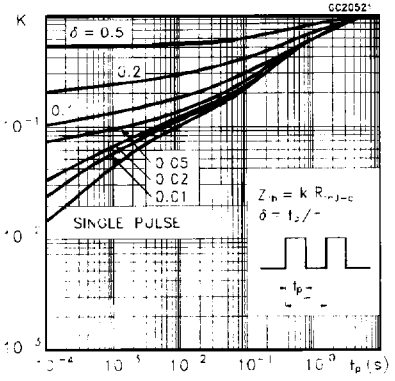
Safe Operating Areas For ISOWATT220



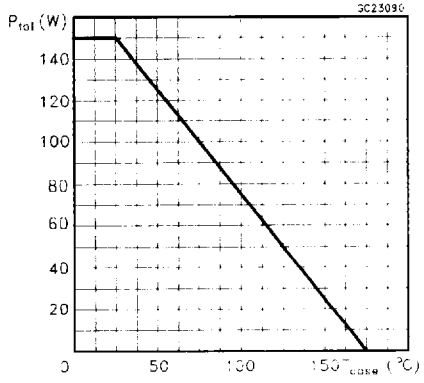
Thermal Impedance For TO-220



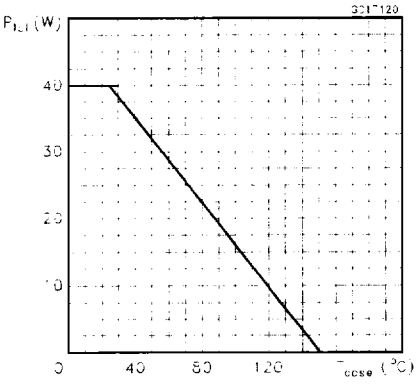
Thermal Impedance For ISOWATT220



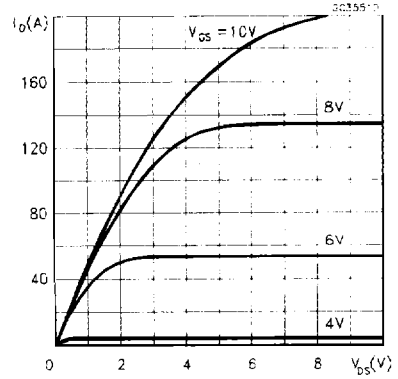
Derating Curve For TO-220



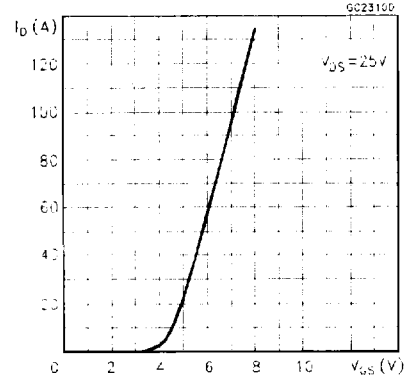
Derating Curve For ISOWATT220



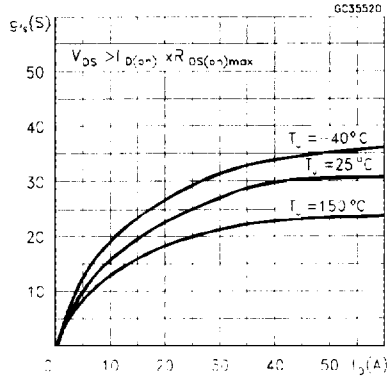
Output Characteristics



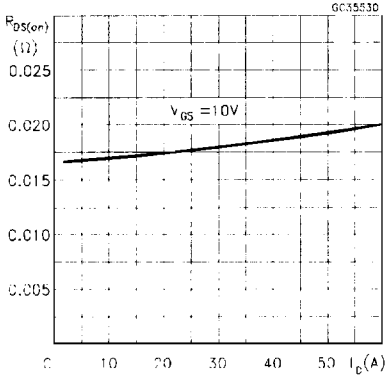
Transfer Characteristics



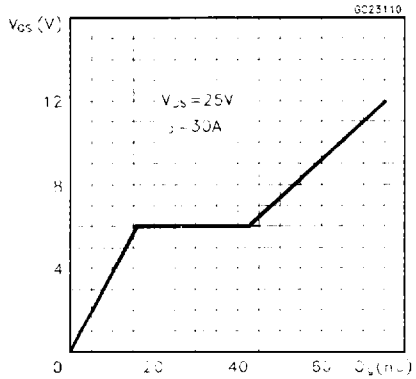
Transconductance



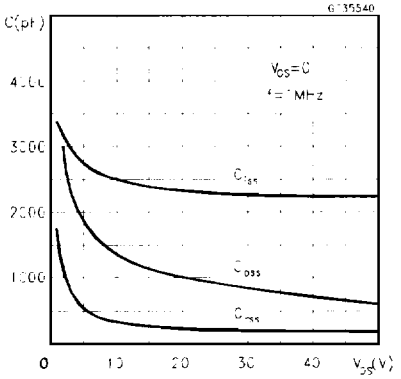
Static Drain-source On Resistance



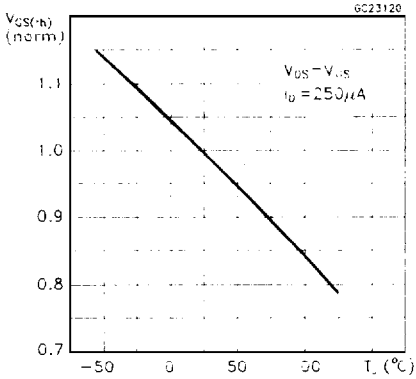
Gate Charge vs Gate-source Voltage



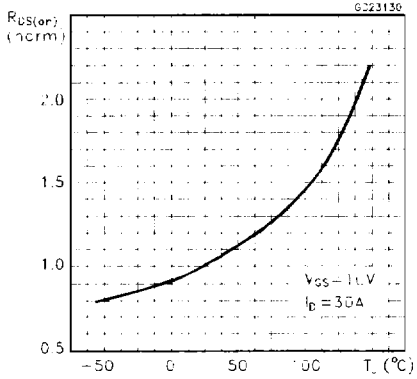
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

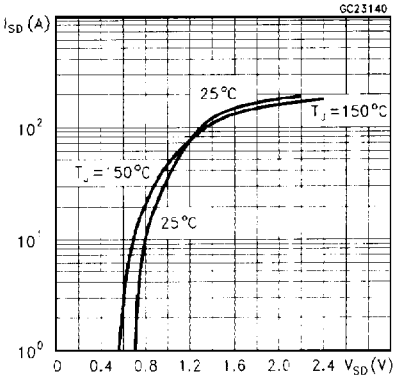


Fig. 2: Unclamped Inductive Waveforms

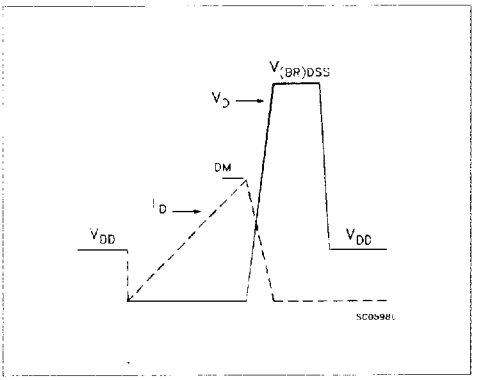


Fig. 1: Unclamped Inductive Load Test Circuits

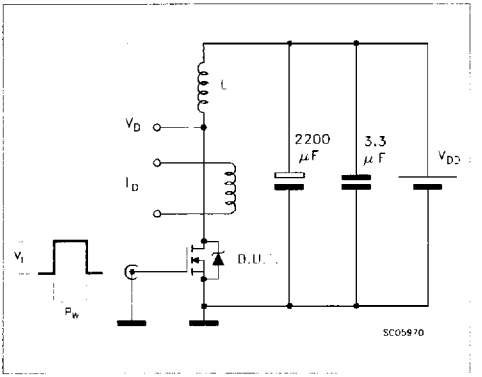


Fig. 3: Switching Times Test Circuits For Resistive Load

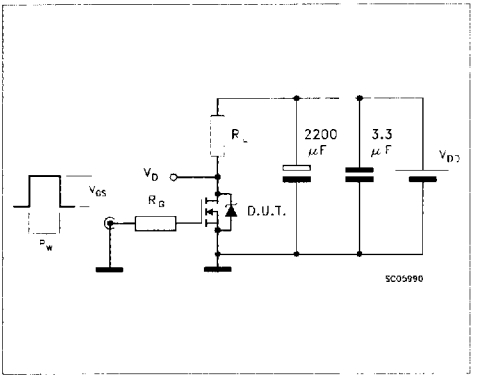


Fig. 4: Gate Charge Test Circuit

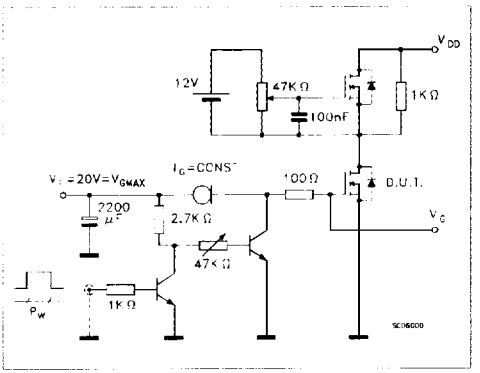
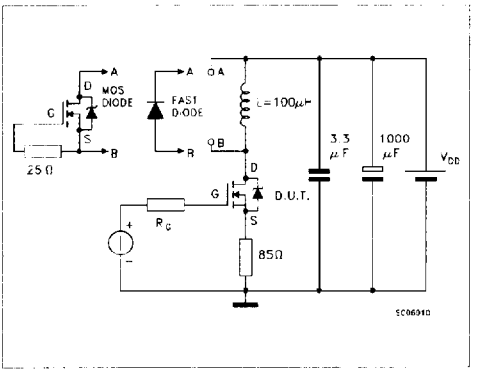


Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time



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